

CLAIMS

1. A light-emitting device comprising:

a wiring formed on a first film;

a second film formed of the same layer as the wiring on the first film;

5 a third film formed over the first film; and

an electrode of a light-emitting element formed on the third film,

wherein the electrode of the light-emitting element is formed so that at least a portion of the electrode of the light-emitting element is overlapped with the second film, and

10 wherein an opening of a fourth film covering an edge of the electrode of the light-emitting element is provided in an overlap portion of the electrode of the light-emitting element and the second film.

2. The light-emitting device according to claim 1, wherein a reflective film is included in the electrode of the light-emitting element.

15 3. The light-emitting device according to claim 1 or claim 2, wherein the wiring is integrated with the second film.

4. The light-emitting device according to claim 1, wherein the second film has a film thickness equal to or thicker than that of the wiring.

5. A light-emitting device comprising:

20 a transistor including a semiconductor film, a gate insulating film, and a gate electrode;

a first film formed on the transistor;

a wiring formed on the first film

a second film formed of the same layer as the wiring on the first film;

25 a third film formed over the first film; and

an electrode of a light-emitting element formed on the third film,

wherein the electrode of the light-emitting element is formed so that at least a portion of the electrode of the light-emitting element is overlapped with the second film, and

30 wherein an opening of a fourth film covering an edge of the electrode of the

light-emitting element is provided in an overlap portion of the electrode of the light-emitting element and the second film.

6. The light-emitting device according to claim 5, wherein a reflective film is included in the electrode of the light-emitting element.

5 7. The light-emitting device according to claim 5 or claim 6, wherein the wiring is integrated with the second film.

8. The light-emitting device according to claim 5, wherein the second film has a film thickness equal to or thicker than that of the wiring.

9. A light-emitting device comprising:

10 a semiconductor film;

a gate insulating film formed on the semiconductor film;

a gate electrode formed on the gate insulating film;

a first film formed on the gate electrode;

a wiring formed on the first film

15 a second film formed of the same layer as the wiring on the first film;

a third film formed over the first film; and

an electrode of a light-emitting element formed on the third film,

wherein the electrode of the light-emitting element is formed so that at least a portion of the electrode of the light-emitting element is overlapped with the second film,

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wherein an opening of a fourth film covering an edge of the electrode of the light-emitting element is provided in an overlap portion of the electrode of the light-emitting element and the second film.

10. The light-emitting device according to claim 9, wherein a reflective film is provided
25 in the electrode of the light-emitting element.

11. The light-emitting device according to claim 9 or claim 10, wherein the wiring is integrated with the second film.

12. The light-emitting device according to claim 9, wherein the second film has a film thickness equal to or thicker than that of the wiring.

30 13. A light-emitting device comprising:

a wiring formed on a first interlayer insulating film;
a conductive film formed of the same layer as the wiring on the first interlayer insulating film;

5 a second interlayer insulating film formed over the first interlayer insulating film; and

an electrode of a light-emitting element formed on the second interlayer insulating film;

wherein the electrode of the light-emitting element is formed so that at least a portion of the electrode of the light-emitting element is overlapped with the conductive
10 film, and

wherein an opening of a partition layer covering an edge of the electrode of the light-emitting element is provided in an overlap portion of the electrode of the light-emitting element and the conductive film.

14. A method of manufacturing a light-emitting device, comprising:

15 a process of forming a first interlayer insulating film;
a process of forming a wiring and a conductive film on the first interlayer insulating film;

a process of forming a second interlayer insulating film over the first interlayer insulating film; and

20 a process of forming an electrode of a light-emitting element on the second interlayer insulating film so that at least a portion of the light-emitting element is overlapped with the conductive film with the second interlayer insulating film interposed therebetween;

a process of forming a partition layer that has an opening in an overlap portion
25 of the conductive film and the light-emitting element.

15. The method of manufacturing the light-emitting device according to claim 14, further comprises a process of planarizing locally a surface of the second interlayer insulating film to planarize at least the overlap portion with the conductive film.

16. A method of manufacturing a light-emitting device, comprising:

30 a process of forming a semiconductor film;

a process of forming a gate insulating film on the semiconductor film;
a process of forming a gate electrode on the gate insulating film;
a process of forming a first interlayer insulating film on the gate electrode;
a process of forming a wiring and a conductive film on the first interlayer

5 insulating film;

a process of forming a second interlayer insulating film over the first interlayer insulating film; and

a process of forming an electrode of a light-emitting element on the second interlayer insulating film so that at least a portion of the light-emitting element is
10 overlapped with the conductive film with the second interlayer insulating film interposed therebetween;

a process of forming a partition layer that has an opening in an overlap portion of the conductive film and the light-emitting element.

17. The method of manufacturing the light-emitting device according to claim 16,
15 further comprises a process of planarizing locally a surface of the second interlayer insulating film to planarize at least the overlap portion with the conductive film.

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